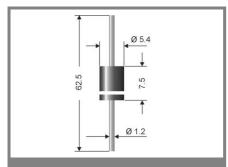
BY 550-50...BY 550-1000



Axial lead diode

Standard silicon rectifier diodes

BY 550-50...BY 550-1000

Forward Current: 5 A

Reverse Voltage: 50 to 1000 V

Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

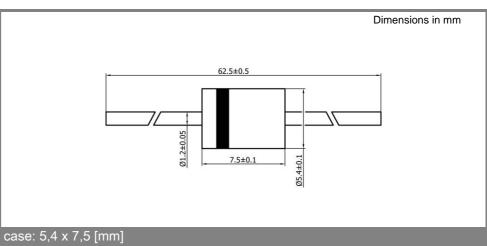
Mechanical Data

- Plastic case 5.4 x 7.5 [mm]
- Weight approx.: 1,4 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 1250 pieces per ammo
- 1) Valid, if leads are kept at ambient temperature at a distance of 10 mm from
- 2) I_F=5A, T_i=25°C
- 3) T_A = 25 °C

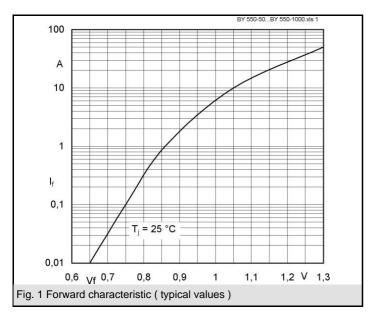
| Туре | Repetitive peak reverse voltage | Surge peak reverse voltage | Max. reverse recovery time | Max. forward voltage |
|-------------|---------------------------------|----------------------------|---|------------------------------|
| | V | V | I _F = - A I _R = - A I _{RR} = - A | |
| | V _{RRM} V | V _{RSM} V | t _{rr} ns | V _F ²⁾ |
| BY 550-50 | 50 | 50 | - | 1,0 |
| BY 550-100 | 100 | 100 | - | 1,0 |
| BY 550-200 | 200 | 200 | - | 1,0 |
| BY 550-400 | 400 | 400 | - | 1,0 |
| BY 550-600 | 600 | 600 | - | 1,0 |
| BY 550-800 | 800 | 800 | - | 1,0 |
| BY 550-1000 | 1000 | 1000 | - | 1,0 |

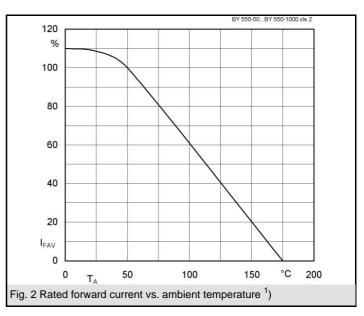
| Absolute Maximum Ratings Tc = 25°C, unless otherwise specified | | | | |
|---|--|---------|-------|--|
| Symbol | Conditions | Values | Units | |
| I_{FAV} | Max. averaged fwd. current, R-load, T _A = 50 °C ¹⁾ | 5 | Α | |
| I _{FRM} | Repetitive peak forward current f > 15 Hz ¹⁾ | 60 | Α | |
| I _{FSM} | Peak forward surge current 50 Hz half sinus-wave 3) | 300 | Α | |
| i²t | Rating for fusing, t < 10 ms ³⁾ | 450 | A²s | |
| R _{thA} | Max. thermal resistance junction to ambient 1) | 25 | K/W | |
| R _{thT} | Max. thermal resistance junction to terminals 1) | - | K/W | |
| T _j | Operating junction temperature | -50+175 | °C | |
| T _s | Storage temperature | -50+175 | °C | |

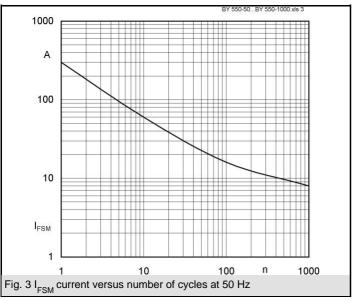
| Characte | racteristics Tc = 25°C, unless otherwise speci | | ecified |
|------------------|--|--------|---------|
| Symbol | Conditions | Values | Units |
| I_R | Maximum leakage current, $T_j = 25$ °C; $V_R = V_{RRM}$ | 20 | μA |
| | $T_j = {^{\circ}C}; V_R = V_{RRM}$ | | |
| CJ | Typical junction capacitance | - | pF |
| | (at MHz and applied reverse voltage of V) | | |
| Q_{rr} | Reverse recovery charge | - | μC |
| | $(U_R = V; I_F = A; dI_F/dt = A/ms)$ | | |
| E _{RSM} | Non repetitive peak reverse avalanche energy | - | mJ |
| | $(I_R = mA; T_j = ^{\circ}C; inductive load switched off)$ | | |



BY 550-50...BY 550-1000







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